

EXHIBIT N

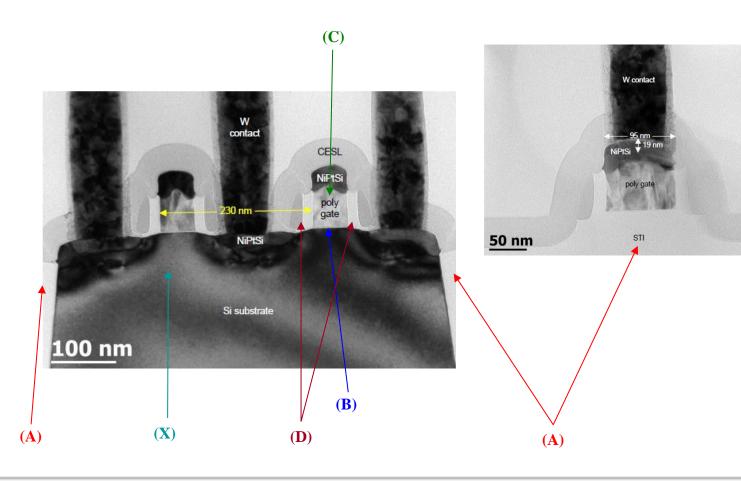
- 1. A semiconductor device, comprising:
- (A) a trench isolation surrounding (X) an active area of a semiconductor substrate;
- **(B)** a gate insulating film formed over the active area;
- (C) a gate electrode formed over the gate insulating film;
- (D) first L-shaped sidewalls formed over the side surfaces of the gate electrode;
- (E) first silicide layers formed on regions located on the sides of the first L-shaped sidewalls within the active area[;]
- (F) an interconnection formed on the trench isolation; and
- (G) second L-shaped sidewalls formed over the side surfaces of the interconnection.



Case 1: <u>frantyb002901/MP17, Decurrene Otralini/Asidii lect-0A/R2/126 InRagrev8858 & Fragrel D</u> #: 296

Claim 1

A semiconductor device, comprising: (A) a trench isolation surrounding (X) an active area of a semiconductor substrainsulating film formed over the active area; (C) a gate electrode formed over the gate insulating film; (D) first L-shap formed over the side surfaces of the gate electrode;

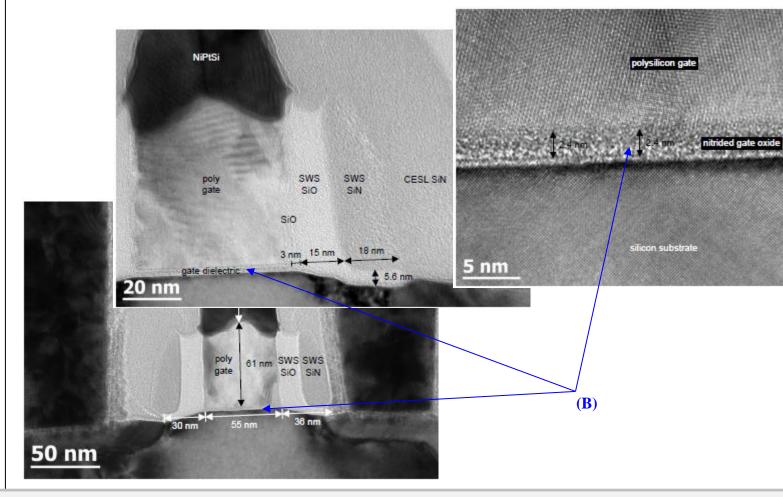




Case 1: <u>transvirus 00 290 vivin 7, Decuma e otnimital si dri bede 04/12/2/12/6 in Ragov 88 set (p Pragos) p</u> #: 297

Claim 1

A semiconductor device, comprising: (A) a trench isolation surrounding (X) an active area of a semiconductor substrainsulating film formed over the active area; (C) a gate electrode formed over the gate insulating film; (D) first L-shap formed over the side surfaces of the gate electrode;





Case 1: <u>franco 10200 (No. 17, Decuman e Otralinal Asia Filippe DAGRAGIA G In Ragon 88.58 (P. Pragon ID</u> #: 298

Claim 1

(E) first silicide layers formed on regions located on the sides of the first L-shaped sidewalls within the active area[;] (interconnection formed on the trench isolation; and (G) second L-shaped sidewalls formed over the side surfaces of the interconnection.

